

Semiconductors
High-reliability discrete products and engineering services since 1977

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS ( $\mathrm{Sn} / \mathrm{Pb}$ plating), standard, and as RoHS by adding "-PBF" suffix.


## MAXIMUM RATINGS

| Parameter | Symbol | 2SC1325A | Unit |
| :---: | :---: | :---: | :---: |
| Collector-base voltage | $V_{\text {сво }}$ | 1500 | V |
| Collector-emitter voltage | Vceo | 600 | V |
| Emitter-base voltage | $\mathrm{V}_{\text {Ebo }}$ | 6.0 | V |
| Collector current - continuous | Ic | 6.0 | A |
| Collector current - peak | 1 Icm | 12 | A |
| Base current | $\mathrm{I}_{\mathrm{B}}$ | 2.0 | A |
| Total power dissipation Derate above $25^{\circ} \mathrm{C}$ | PD | $\begin{gathered} \hline 80 \\ 0.64 \end{gathered}$ | $\begin{gathered} \mathrm{W} \\ \mathrm{~W} /{ }^{\circ} \mathrm{C} \\ \hline \end{gathered}$ |
| Junction and storage temperature range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to 150 | ${ }^{\circ} \mathrm{C}$ |
| Thermal resistance, junction to case | Reлс | 1.56 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Parameter | Symbol | Conditions | 2SC1325A |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Max |  |
| Collector-emitter voltage | Vceo | $\mathrm{I}_{\mathrm{c}}=100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | 600 | - | V |
| Collector cutoff current | $I_{\text {ceo }}$ | $\mathrm{V}_{\text {CE }}=1500 \mathrm{~V}, \mathrm{~V}_{\mathrm{BE}}=0$ | - | 1.0 | mA |
| Collector cutoff current | Icbo | $\mathrm{V}_{C E}=1500 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ | - | 20 | $\mu \mathrm{A}$ |
| Emitter cutoff current | $\mathrm{I}_{\text {Ebo }}$ | $\mathrm{V}_{\mathrm{EB}}=5 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0$ | - | 200 | $\mu \mathrm{A}$ |
| DC current gain | $h_{\text {fe }}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=1.0 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=15 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=5.0 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=15 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & 10 \\ & 5.0 \end{aligned}$ | $\begin{aligned} & 45 \\ & 35 \end{aligned}$ | - |
| Collector-emitter saturation voltage | $\mathrm{V}_{\text {CE(sat) }}$ | $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=1.2 \mathrm{~mA}$ | - | 4.0 | V |
| Base-emitter saturation voltage | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=1.2 \mathrm{~mA}$ | - | 1.1 | V |
| Storage time | $\mathrm{t}_{5}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=5.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B} 1}=-\mathrm{i}_{\mathrm{B} 2}=1.0 \mathrm{~A}, \mathrm{Pw}= \\ & 20 \mu \mathrm{sw} \end{aligned}$ | - | 10 | $\mu \mathrm{s}$ |
| Fall time | $\mathrm{t}_{\mathrm{f}}$ |  | - | 0.8 | $\mu \mathrm{s}$ |

$\because$ CHITMOM-
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2SC1325A

SILICON NPN TRANSISTOR

MECHANICAL CHARACTERISTICS

| Case: | TO-3 |
| :--- | :--- |
| Marking: | Alpha-Numeric |
| Polarity: | See below |



FIGURE -1 POWER DERATING


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## ACTIVE-REGION SAFE OPERATING AREA (SOA)




SWITCHING TIME- AMBLENT TEMPERATURE



COLLECTOR SATURATION REGION

b. BASE CURRENT ( $A$ )

